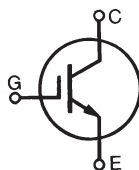


High Voltage IGBT

MMIX1G75N250

For Capacitor Discharge Applications

(Electrically Isolated Tab)

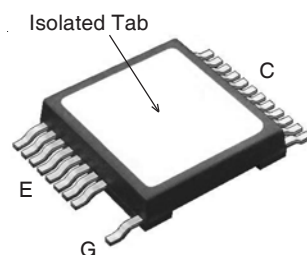
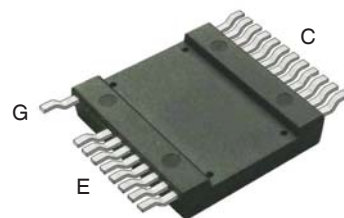


$$V_{CES} = 2500V$$

$$I_{C90} = 65A$$

$$V_{CE(sat)} \leq 2.9V$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	2500	V
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	2500	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	110	A
I_{C90}	$T_C = 90^\circ C$	65	A
I_{CM}	$T_C = 25^\circ C$, $V_{GE} = 20V$, 1ms	580	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$	$I_{CM} = 200$	A
(RBSOA)	Clamped Inductive Load	$V_{CE} \leq 0.8 \cdot V_{CES}$	
P_C	$T_C = 25^\circ C$	430	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10s	260	$^\circ C$
V_{ISOL}	50/60Hz, 1 minute	2500	V~
F_C	Mounting Force	50..200 / 11..45	N/lb.
Weight		8	g



G = Gate E = Emitter
C = Collector

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- High Peak Current Capability
- Low Saturation Voltage
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Applications

- Capacitor Discharge
- Pulser Circuits

Advantages

- High Power Density
- Easy to Mount

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 4mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ Note 2, $T_J = 125^\circ C$			50 μA 5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = 75A$, $V_{GE} = 15V$, Note 1		2.5	V
	$I_C = 300A$, $V_{GE} = 25V$		4.1	V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 1	35	58	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		9000	pF
C_{oes}			345	pF
C_{res}			110	pF
$Q_{g(on)}$	$I_C = 75\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		410	nC
Q_{ge}			63	nC
Q_{gc}			175	nC
$t_{d(on)}$	Resistive Switching Times $I_C = 150\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}$, $R_G = 1\Omega$		55	ns
t_r			225	ns
$t_{d(off)}$			270	ns
t_f			455	ns
R_{thJC}				0.29 $^\circ\text{C/W}$
R_{thCK}		0.05		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Part must be heatsunk for high-temp I_{ces} measurement.

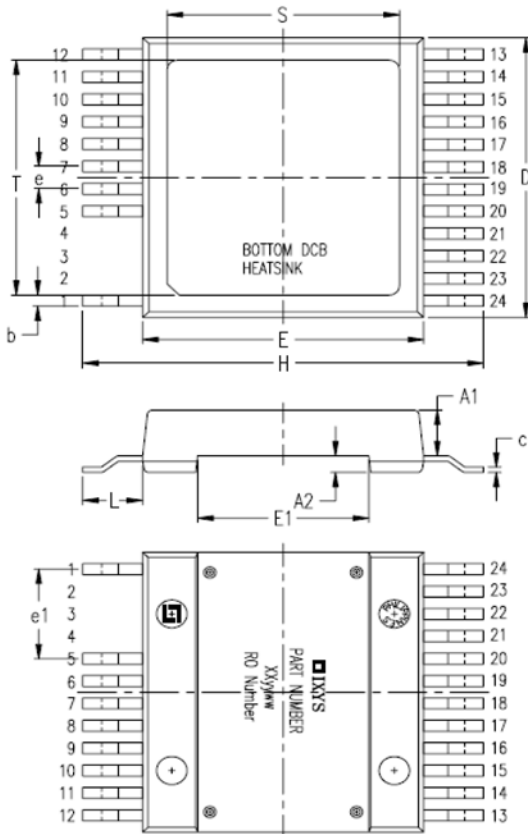
ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.209	.224	5.30	5.70
A1	.154	.161	3.90	4.10
A2	.055	.063	1.40	1.60
b	.035	.045	0.90	1.15
c	.018	.026	0.45	0.65
D	.976	.994	24.80	25.25
E	.898	.915	22.80	23.25
E1	.543	.559	13.80	14.20
e	.079 BSC		2.00 BSC	
e1	.315 BSC		8.00 BSC	
H	1.272	1.311	32.30	33.30
L	.181	.209	4.60	5.30
L1	.051	.067	1.30	1.70
L2	.000	.006	0.00	0.15
S	.736	.760	18.70	19.30
T	.815	.839	20.70	21.30
α	0	4°	0	4°

PIN: 1 = Gate
5-12 = Emitter
13-24 = Collector

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

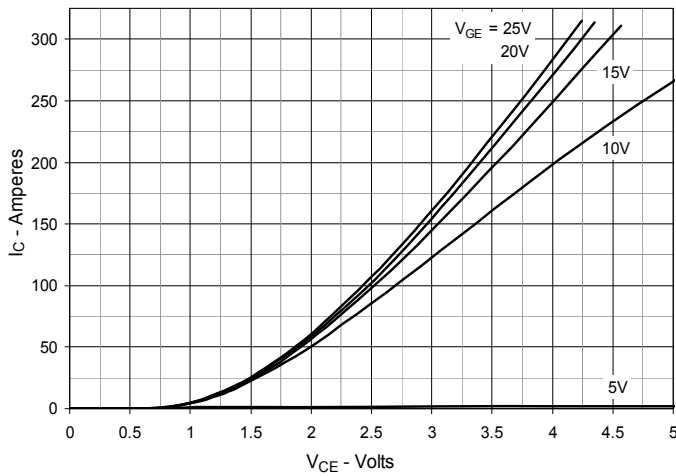


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

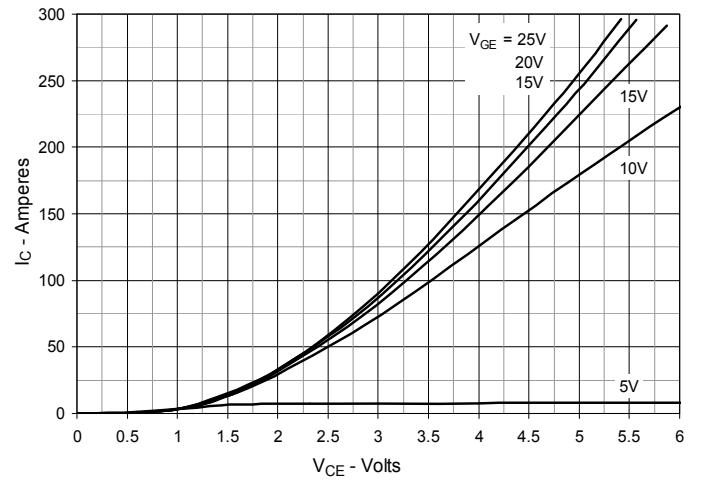


Fig. 3. Dependence of $V_{CE(sat)}$ on Junction Temperature

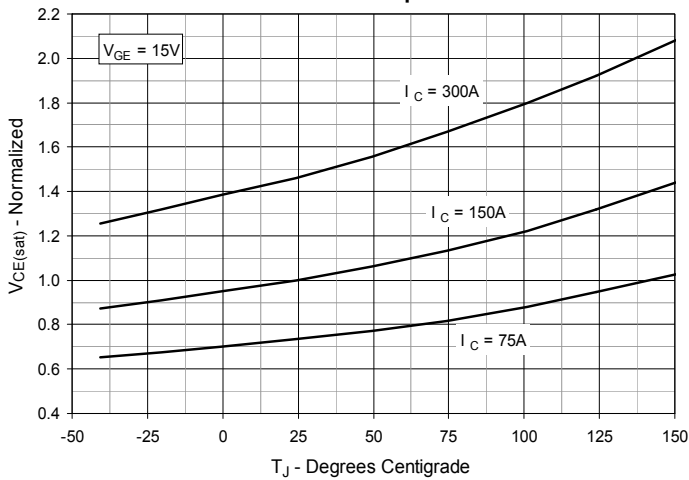


Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

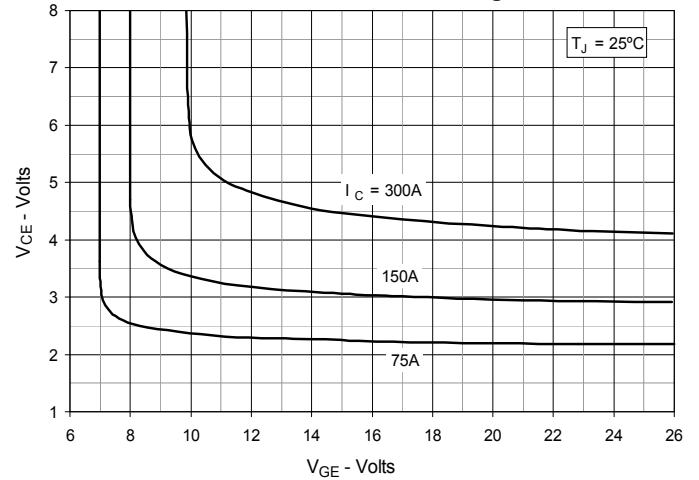


Fig. 5. Input Admittance

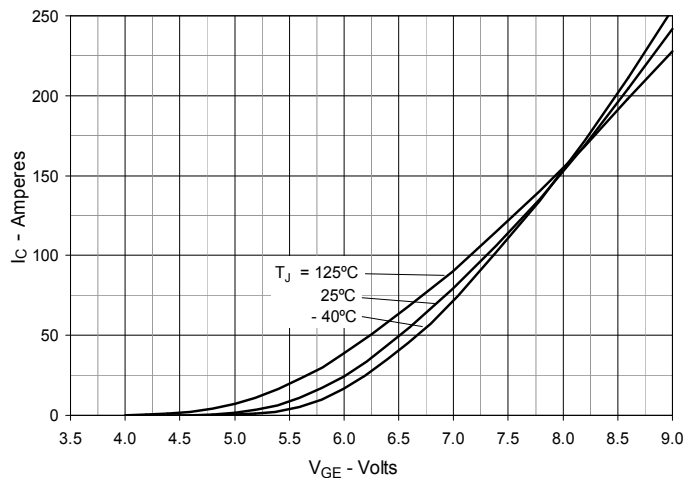


Fig. 6. Transconductance

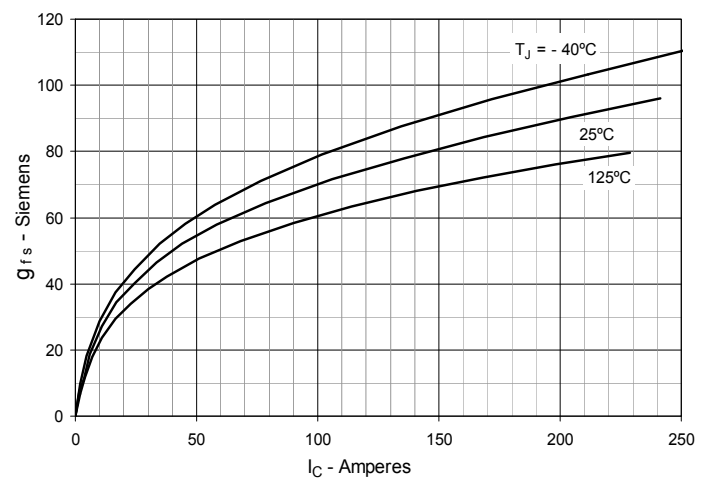


Fig. 7. Gate Charge

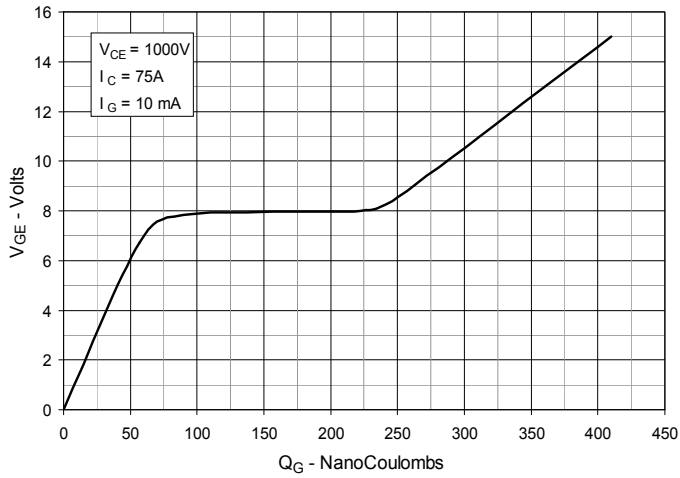


Fig. 8. Capacitance

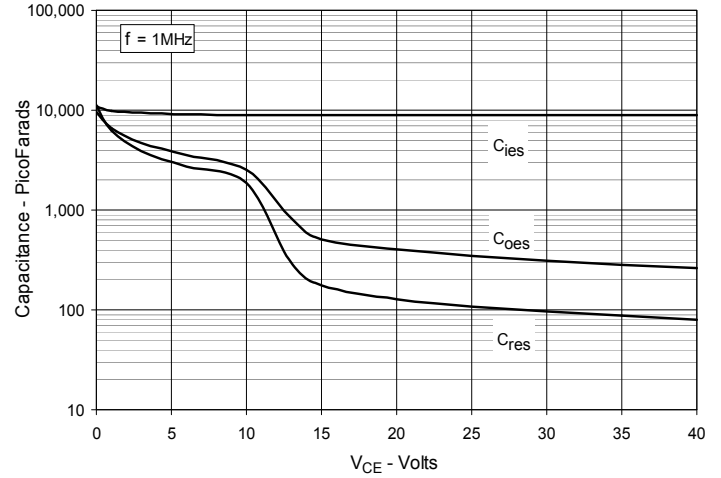


Fig. 9. Reverse-Bias Safe Operating Area

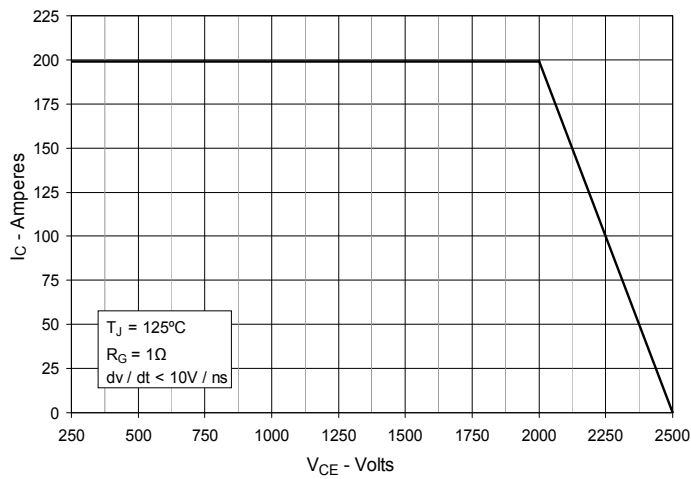


Fig. 10. Maximum Transient Thermal Impedance

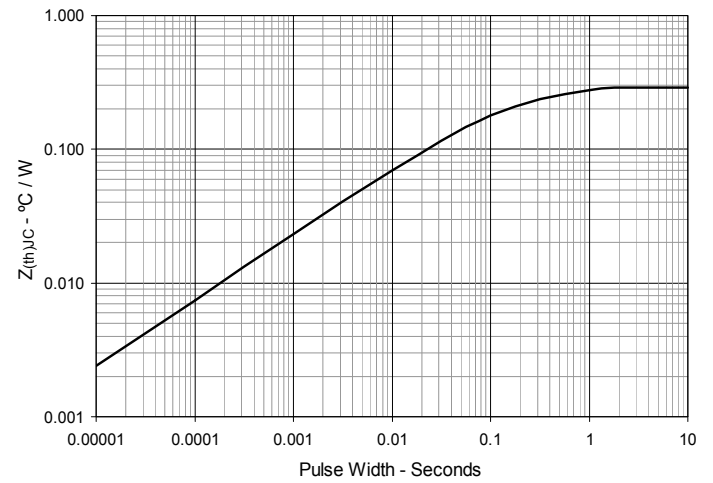


Fig. 11. Resistive Turn-on Rise Time vs. Junction Temperature

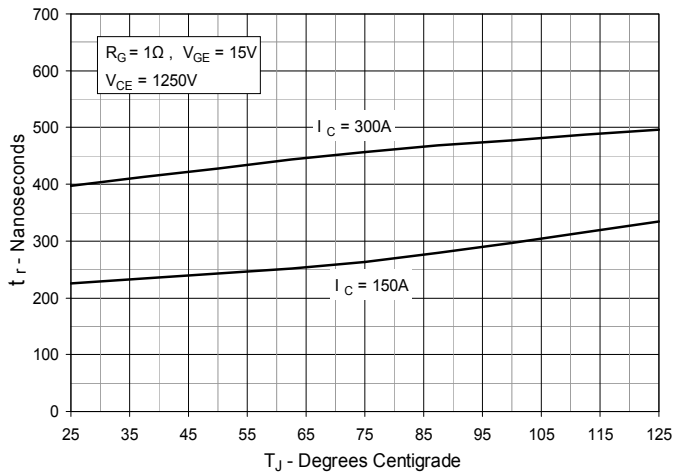


Fig. 12. Resistive Turn-on Rise Time vs. Collector Current

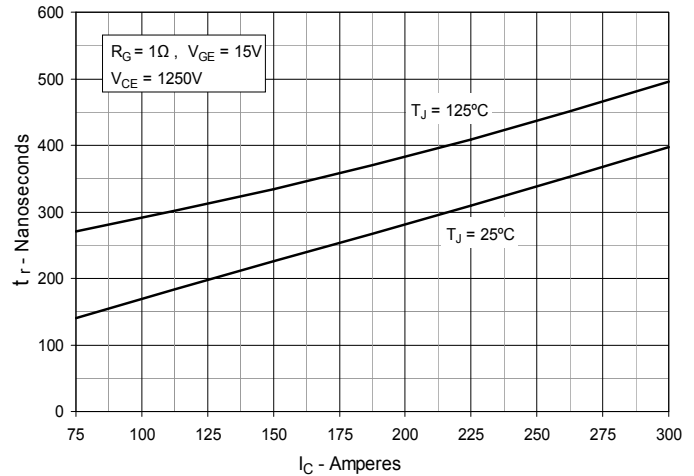


Fig. 13. Resistive Turn-on Switching Times vs. Gate Resistance

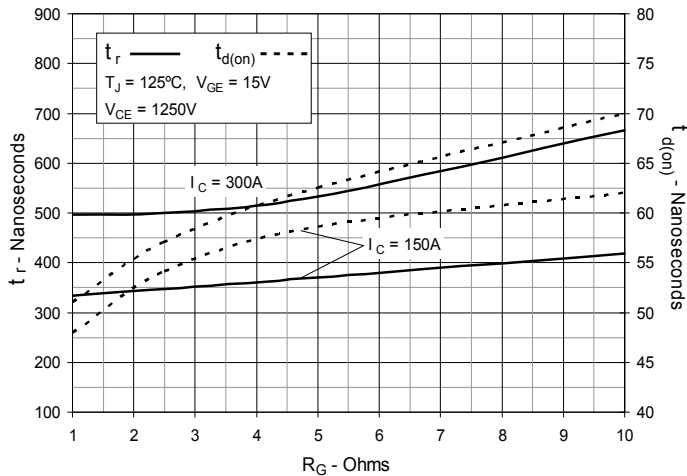


Fig. 14. Resistive Turn-off Switching Times vs. Junction Temperature

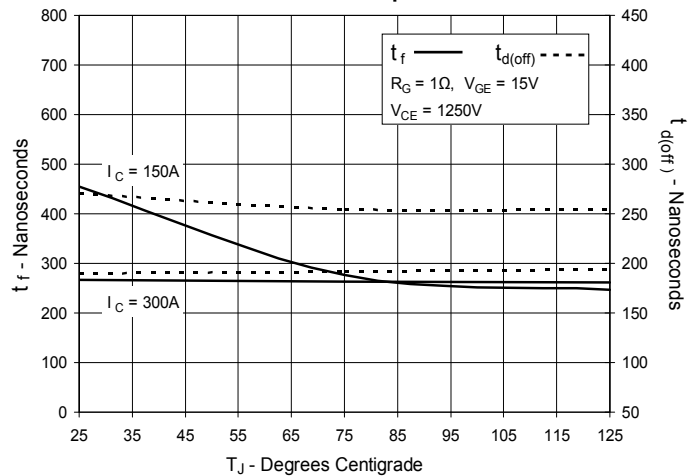


Fig. 15. Resistive Turn-off Switching Times vs. Collector Current

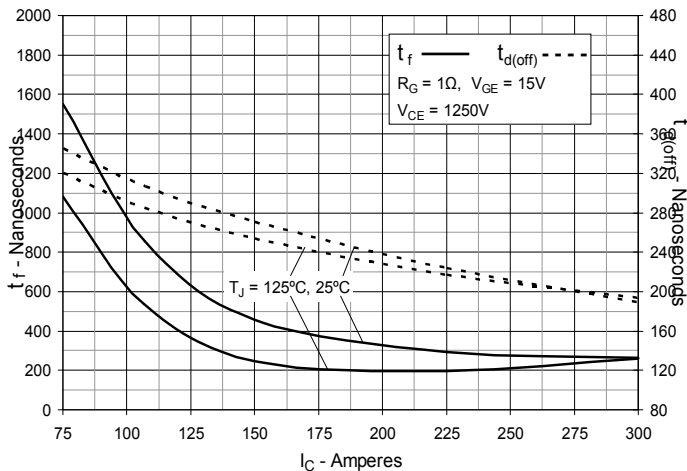
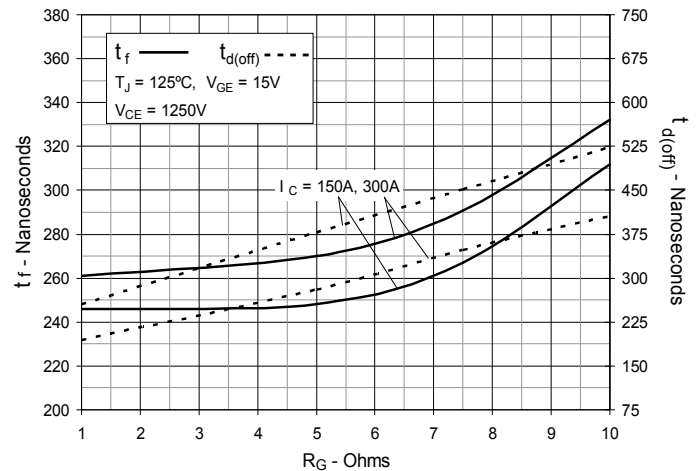


Fig. 16. Resistive Turn-off Switching Times vs. Gate Resistance





Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.